



Contents lists available at ScienceDirect

Materials Science & Engineering B

 journal homepage: www.elsevier.com/locate/mseb


Ion beam irradiation: Novel approach for preparation of Ag coated N doped nanocrystalline anatase TiO₂ films

 P.N. Wani^a, S.K. Kale^b, S.S. Dahiwalé^c, Umesh T. Nakate^{d,e}, S.U. Ekar^f, Yogesh T. Nakate^g, P.S. More^h, M.T. Sarodeⁱ, Y.B. Khollam^{e,*}
^a Department of Physics, Prof. Ramkrishna Muni ACS College, Akurdi, Pune 412 044, Maharashtra, India

^b Department of Applied Science, Pimpri Chinchwad College of Engineering, Nigadi, Pune 412 044, Maharashtra, India

^c Department of Physics, Savitribai Phule Pune University, Ganeshkhind, Pune 412 007, India

^d Department of Polymer-Matrix Science and Technology, Jambik National University (JNU), Jambik-51, Anilshah-40, Republic of Korea

^e Department of Physics, Bhatnagar College, Sangli, Pune 412 027, Maharashtra, India

^f Department of Electronics, K.J.SOM University, Jalgaon 426 901, Maharashtra, India

^g Nanomaterials Application Laboratory, The Institute of Science, Dr. Homi Bhabha State University, Mumbai 400 032, Maharashtra, India

^h Department of Physics, Mahatma Jyoti Bahadur College, Pimpri, Pune 412 017, Maharashtra, India

ARTICLE INFO
Keywords:

 Anatase TiO₂
 N:Ag doped TiO₂
 Nitrogen irradiation, Electrochemical
 Impedance Spectroscopy (EIS)
 Raman spectroscopy

ABSTRACT

Herein, a novel approach of ion beam irradiation (nitrogen beam dose $\sim 10^{18}$ ions/cm², 40 keV for 30 min in ultra-high vacuum conditions) is explored for the preparation of nanocrystalline anatase TiO₂ modified with nitrogen (N) and silver (Ag). The prepared materials characterized using XRD, Raman, UV-Visible spectroscopy, EIS and wettability techniques. The structural-optical studies revealed the intentional and/or substitutional doping of N in O-Ti-O matrix supported by Williamson-Hall lattice strain values and dispersion of Ag⁺ particles at the TiO₂ surface. Raman spectra confirmed the crystallization of anatase TiO₂ wherein red shifting/broadening of Raman active modes are due to the phonon confinement and structural defects due to favored substitutional N³⁻ doping in TiO₂ lattice. The higher values of χ^2 , Z², and R_{ct} in Nyquist plots and the blue shift of ω_{Mn} in Bode plots for irradiated film further supported the substitutional doping of N rather than the interstitial one.

1. Introduction

In the era of modern advanced technology, the step towards the fabrication of new functional devices is one of the most important revolutions. The metal, as well as semiconductor oxides having remarkable properties, play a leading role in this process of device fabrication [1,2]. Among these oxides, because of the high chemical stability, low cost, better biocompatibility, long-term photo-stability, strong oxidized stability, high thermal stability, and non-toxicity properties, titanium dioxide (TiO₂) is noted to be an important semiconductor oxide. Due to this, a significant amount of research on TiO₂ has been carried out over the last few decades for its potential applications ranging from energy to environmental aspects [3–5]. The semiconductor TiO₂ is proved to be a very useful oxide in many fields like antibacterial applications [6,7], sensors [8,9], photocatalysis for environmental purification, and production of hydrogen from water [10–13], removal of unwanted impurities from water and air [14,15], solar cells [16,17], ceramic membrane

and also as a catalyst for photocatalytic decomposition [18–21].

Different nanostructures like nanofibers [19,21] nanowires [22–24], nanotubes [25,26], nanorods [27,28], nanospheres [29], nanoplates [30] are synthesized for improving the properties of the TiO₂. Doping with metal or nonmetal in TiO₂ may be an effective solution to expand its properties in various fields. The addition of ion impurity incorporated in TiO₂ is more beneficial to amend physicochemical properties such as optoelectronic property, photocatalytic property, photovoltaic property, etc. [31–33]. Diverse metal (transition metals: Co, Cu, Ni, Cr, Mn, Mo, Nb, V, Fe, Ru, noble metals: Pt, Ag, Au) or nonmetal (e.g. B, S, P, C, N, F, I) ion implantation in TiO₂ is a good practice for the researcher to tune its optical, electrical, photocatalytic and magnetic properties [31]. Lots of procedures such as ion-assisted sputtering, chemical vapor deposition, sol-gel, chemical mixing, magnetron sputtering, and ion implantation [33,34–38] were adapted by researchers for doping the TiO₂.

TiO₂ is a promising photocatalyst in the ultraviolet region. The nitrogen-doped TiO₂ lowers the bandgap of TiO₂, showing good

^{*} Corresponding author.

 E-mail addresses: sarode.nakate@pccae.ac.in, umesh.nakate@gnul.ac.in (U.T. Nakate), ybkhollam@pccae.ac.in (Y.B. Khollam).